

DATA SHEET

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74HC1G125; 74HCT1G125 Bus buffer/line drivers; 3-state

Product specification
Supersedes data of 2002 May 17

2004 Jul 27

Bus buffer/line drivers; 3-state

74HC1G125; 74HCT1G125

FEATURES

- Wide supply voltage range from 2.0 to 6.0 V
- Symmetrical output impedance
- High noise immunity
- Low power dissipation
- Balanced propagation delays
- Very small 5 pins package
- Output capability: bus driver.

DESCRIPTION

The 74HC1G/HCT1G125 is a high-speed Si-gate CMOS device.

The 74HC1G/HCT1G125 provides one non-inverting buffer/line driver with 3-state output. The 3-state output is controlled by the output enable input pin (\overline{OE}). A HIGH at pin \overline{OE} causes the output as assume a high-impedance OFF-state.

The bus driver output currents are equal compared to the 74HC/HCT125.

QUICK REFERENCE DATA

GND = 0 V; $T_{amb} = 25\text{ }^{\circ}\text{C}$; $t_r = t_f \leq 6.0\text{ ns}$.

SYMBOL	PARAMETER	CONDITIONS	TYPICAL		UNIT
			HC1G	HCT1G	
t_{PHL}/t_{PLH}	propagation delay A to Y	$C_L = 15\text{ pF}$; $V_{CC} = 5\text{ V}$	9	10	ns
C_I	input capacitance		1.5	1.5	pF
C_{PD}	power dissipation capacitance	notes 1 and 2	30	27	pF

Notes

1. C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

$$P_D = C_{PD} \times V_{CC}^2 \times f_i + \sum (C_L \times V_{CC}^2 \times f_o) \text{ where:}$$

f_i = input frequency in MHz;

f_o = output frequency in MHz;

C_L = output load capacitance in pF;

V_{CC} = supply voltage in Volts;

$\sum (C_L \times V_{CC}^2 \times f_o)$ = sum of outputs.

2. For HC1G the condition is $V_I = \text{GND to } V_{CC}$.

For HCT1G the condition is $V_I = \text{GND to } V_{CC} - 1.5\text{ V}$.

FUNCTION TABLE

See note 1.

INPUTS		OUTPUT
\overline{OE}	A	Y
L	L	L
L	H	H
H	X	Z

Note

1. H = HIGH voltage level;
L = LOW voltage level;
X = don't care;
Z = high-impedance OFF-state.

Bus buffer/line drivers; 3-state

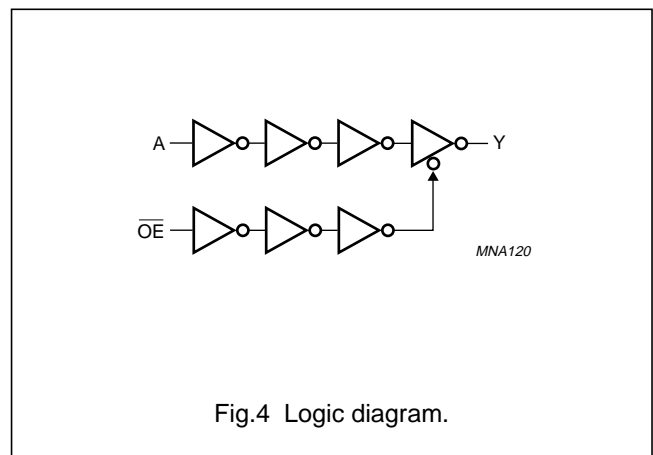
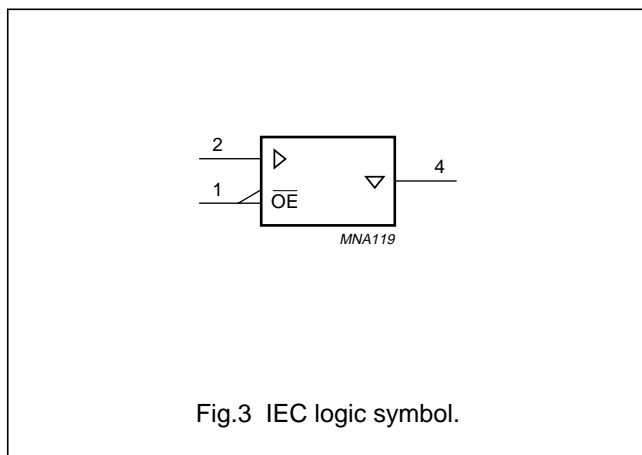
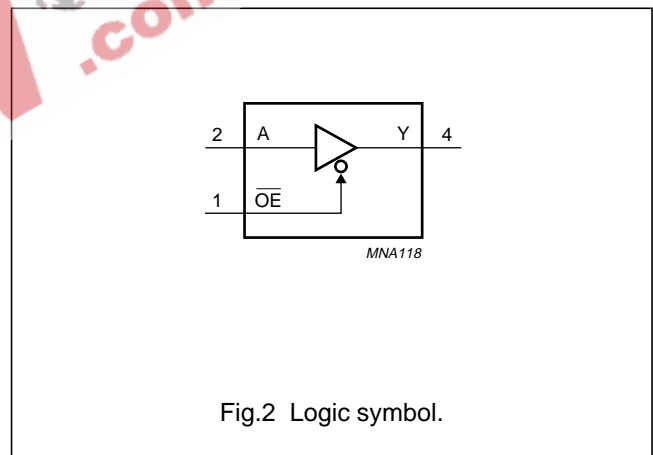
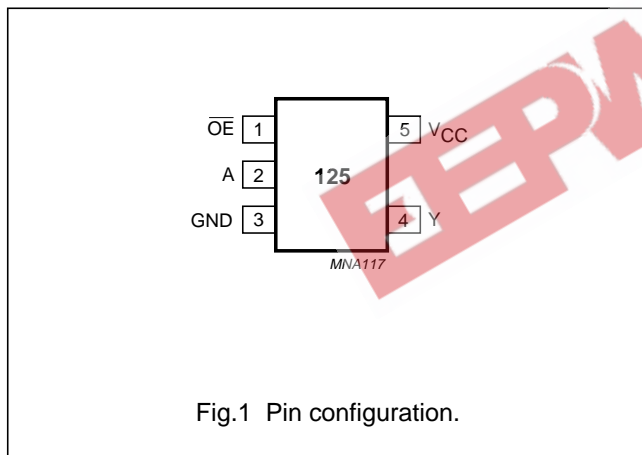
74HC1G125; 74HCT1G125

ORDERING INFORMATION

TYPE NUMBER	PACKAGE					
	TEMPERATURE RANGE	PINS	PACKAGE	MATERIAL	CODE	MARKING
74HC1G125GW	-40 to +125 °C	5	SC-88A	plastic	SOT353	HM
74HCT1G125GW	-40 to +125 °C	5	SC-88A	plastic	SOT353	TM
74HC1G125GV	-40 to +125 °C	5	SC-74A	plastic	SOT753	H25
74HCT1G125GV	-40 to +125 °C	5	SC-74A	plastic	SOT753	T25

PINNING

PIN	SYMBOL	DESCRIPTION
1	\overline{OE}	output enable input
2	A	data input A
3	GND	ground (0 V)
4	Y	data output Y
5	V _{CC}	supply voltage



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RECOMMENDED OPERATING CONDITIONS

SYMBOL	PARAMETER	CONDITIONS	74HC1G125			74HCT1G125			UNIT
			MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
V_{CC}	supply voltage		2.0	5.0	6.0	4.5	5.0	5.5	V
V_I	input voltage		0	–	V_{CC}	0	–	V_{CC}	V
V_O	output voltage		0	–	V_{CC}	0	–	V_{CC}	V
T_{amb}	operating ambient temperature	see DC and AC characteristics per device	–40	+25	+125	–40	+25	+125	°C
t_r, t_f	input rise and fall times	$V_{CC} = 2.0$ V	–	–	1000	–	–	–	ns
		$V_{CC} = 4.5$ V	–	–	500	–	–	500	ns
		$V_{CC} = 6.0$ V	–	–	400	–	–	–	ns

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134); voltages are referenced to GND (ground = 0 V).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CC}	supply voltage		–0.5	+7.0	V
I_{IK}	input diode current	$V_I < -0.5$ V or $V_I > V_{CC} + 0.5$ V; note 1	–	±20	mA
I_{OK}	output diode current	$V_O < -0.5$ V or $V_O > V_{CC} + 0.5$ V; note 1	–	±20	mA
I_O	output source or sink current	-0.5 V < V_O < $V_{CC} + 0.5$ V; note 1	–	±12.5	mA
I_{CC}	V_{CC} or GND current	note 1	–	±25	mA
T_{stg}	storage temperature		–65	+150	°C
P_D	power dissipation per package	for temperature range from –40 to +125 °C; note 2	–	200	mW

Notes

1. The input and output voltage ratings may be exceeded if the input and output current ratings are observed.
2. Above 55 °C the value of P_D derates linearly with 2.5 mW/K.

Bus buffer/line drivers; 3-state

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DC CHARACTERISTICS

Family 74HC1G

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

SYMBOL	PARAMETER	TEST CONDITIONS		T _{amb} (°C)					UNIT
		OTHER	V _{CC} (V)	-40 to +85			-40 to +125		
				MIN.	TYP. ⁽¹⁾	MAX.	MIN.	MAX.	
V _{IH}	HIGH-level input voltage		2.0	1.5	1.2	–	1.5	–	V
			4.5	3.15	2.4	–	3.15	–	V
			6.0	4.2	3.2	–	4.2	–	V
V _{IL}	LOW-level input voltage		2.0	–	0.8	0.5	–	0.5	V
			4.5	–	2.1	1.35	–	1.35	V
			6.0	–	2.8	1.8	–	1.8	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL} ; I _O = -20 μA	2.0	1.9	2.0	–	1.9	–	V
		V _I = V _{IH} or V _{IL} ; I _O = -20 μA	4.5	4.4	4.5	–	4.4	–	V
		V _I = V _{IH} or V _{IL} ; I _O = -20 μA	6.0	5.9	6.0	–	5.9	–	V
		V _I = V _{IH} or V _{IL} ; I _O = -2.0 mA	4.5	4.13	4.32	–	3.7	–	V
		V _I = V _{IH} or V _{IL} ; I _O = -2.6 mA	6.0	5.63	5.81	–	5.2	–	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL} ; I _O = 20 μA	2.0	–	0	0.1	–	0.1	V
		V _I = V _{IH} or V _{IL} ; I _O = 20 μA	4.5	–	0	0.1	–	0.1	V
		V _I = V _{IH} or V _{IL} ; I _O = 20 μA	6.0	–	0	0.1	–	0.1	V
		V _I = V _{IH} or V _{IL} ; I _O = 2.0 mA	4.5	–	0.15	0.33	–	0.4	V
		V _I = V _{IH} or V _{IL} ; I _O = 2.6 mA	6.0	–	0.16	0.33	–	0.4	V
I _{LI}	input leakage current	V _I = V _{CC} or GND	6.0	–	–	1.0	–	1.0	μA
I _{oz}	3-state output current OFF-state	V _I = V _{IH} or V _{IL} ; V _O = V _{CC} or GND	6.0	–	–	5	–	10	μA
I _{CC}	quiescent supply current	V _I = V _{CC} or GND; I _O = 0	6.0	–	–	10	–	20	μA

Note

1. All typical values are measured at T_{amb} = 25 °C.

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Family 74HCT1G

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

SYMBOL	PARAMETER	TEST CONDITIONS		T _{amb} (°C)					UNIT
		OTHER	V _{CC} (V)	-40 to +85			-40 to +125		
				MIN.	TYP. ⁽¹⁾	MAX.	MIN.	MAX.	
V _{IH}	HIGH-level input voltage		4.5 to 5.5	2.0	1.6	–	2.0	–	V
V _{IL}	LOW-level input voltage		4.5 to 5.5	–	1.2	0.8	–	0.8	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL} ; I _O = –20 μA	4.5	4.4	4.5	–	4.4	–	V
		V _I = V _{IH} or V _{IL} ; I _O = –2.0 mA	4.5	4.13	4.32	–	3.7	–	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL} ; I _O = 20 μA	4.5	–	0	0.1	–	0.1	V
		V _I = V _{IH} or V _{IL} ; I _O = 2.0 mA	4.5	–	0.15	0.33	–	0.4	V
I _{LI}	input leakage current	V _I = V _{CC} or GND	5.5	–	–	1.0	–	1.0	μA
I _{OZ}	3-state output current OFF-state	V _I = V _{IH} or V _{IL} ; V _O = V _{CC} or GND	5.5	–	–	5	–	10	μA
I _{CC}	quiescent supply current	V _I = V _{CC} or GND; I _O = 0	5.5	–	–	10	–	20	μA
ΔI _{CC}	additional supply current per input	V _I = V _{CC} – 2.1 V; I _O = 0	4.5 to 5.5	–	–	500	–	850	μA

Note

1. All typical values are measured at T_{amb} = 25 °C.

Bus buffer/line drivers; 3-state

74HC1G125; 74HCT1G125

AC CHARACTERISTICS

Type 74HC1G125

GND = 0 V; $t_r = t_f \leq 6.0$ ns; $C_L = 50$ pF.

SYMBOL	PARAMETER	TEST CONDITIONS		T_{amb} (°C)					UNIT
		WAVEFORMS	V_{CC} (V)	-40 to +85			-40 to +125		
				MIN.	TYP. ⁽¹⁾	MAX.	MIN.	MAX.	
t_{PHL}/t_{PLH}	propagation delay A to Y	see Figs 5 and 7	2.0	–	24	125	–	150	ns
			4.5	–	10	25	–	30	ns
			6.0	–	8	21	–	26	ns
t_{PZH}/t_{PZL}	3-state output enable time \overline{OE} to Y	see Figs 6 and 7	2.0	–	19	155	–	190	ns
			4.5	–	9	31	–	38	ns
			6.0	–	7	26	–	32	ns
t_{PHZ}/t_{PLZ}	3-state output disable time \overline{OE} to Y	see Figs 6 and 7	2.0	–	18	155	–	190	ns
			4.5	–	12	31	–	38	ns
			6.0	–	11	26	–	32	ns

Note

1. All typical values are measured at $T_{amb} = 25$ °C.

Type 74HCT1G125

GND = 0 V; $t_r = t_f \leq 6.0$ ns; $C_L = 50$ pF.

SYMBOL	PARAMETER	TEST CONDITIONS		T_{amb} (°C)					UNIT
		WAVEFORMS	V_{CC} (V)	-40 to +85			-40 to +125		
				MIN.	TYP. ⁽¹⁾	MAX.	MIN.	MAX.	
t_{PHL}/t_{PLH}	propagation delay A to Y	see Figs 5 and 7	4.5	–	11	30	–	36	ns
t_{PZH}/t_{PZL}	3-state output enable time \overline{OE} to Y	see Figs 6 and 7	4.5	–	10	35	–	42	ns
t_{PHZ}/t_{PLZ}	3-state output disable time \overline{OE} to Y	see Figs 6 and 7	4.5	–	11	31	–	38	ns

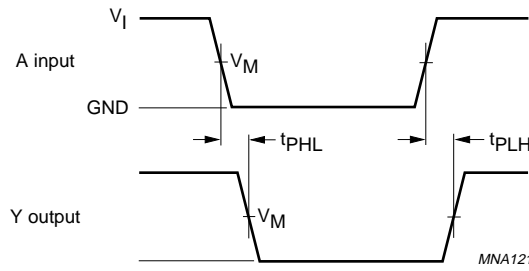
Note

1. All typical values are measured at $T_{amb} = 25$ °C.

Bus buffer/line drivers; 3-state

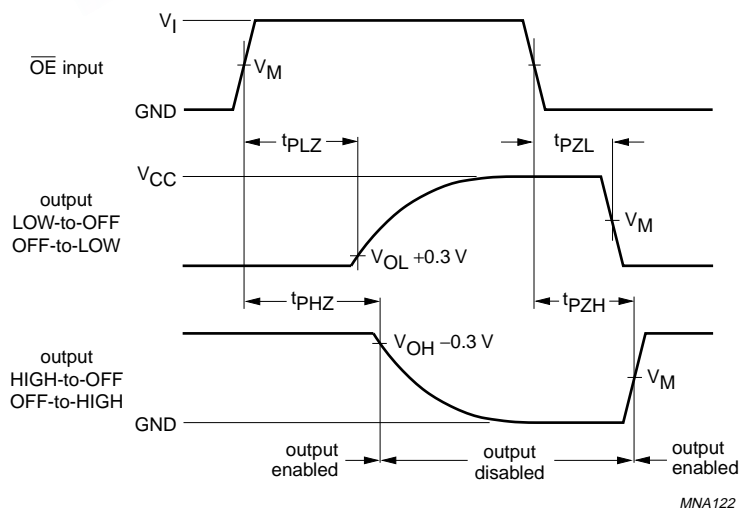
74HC1G125; 74HCT1G125

AC WAVEFORMS



For HC1G: $V_M = 50\%$; $V_I = \text{GND to } V_{CC}$.
 For HCT1G: $V_M = 1.3 \text{ V}$; $V_I = \text{GND to } 3.0 \text{ V}$.

Fig.5 The input (A) to output (Y) propagation delays.

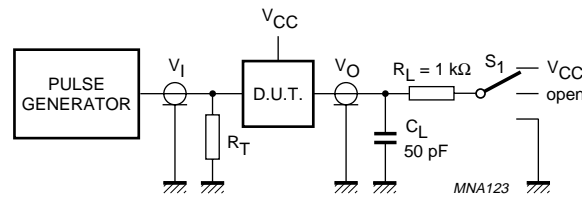


For HC1G: $V_M = 50\%$; $V_I = \text{GND to } V_{CC}$.
 For HCT1G: $V_M = 1.3 \text{ V}$; $V_I = \text{GND to } 3.0 \text{ V}$.

Fig.6 The 3-state enable and disable times.

Bus buffer/line drivers; 3-state

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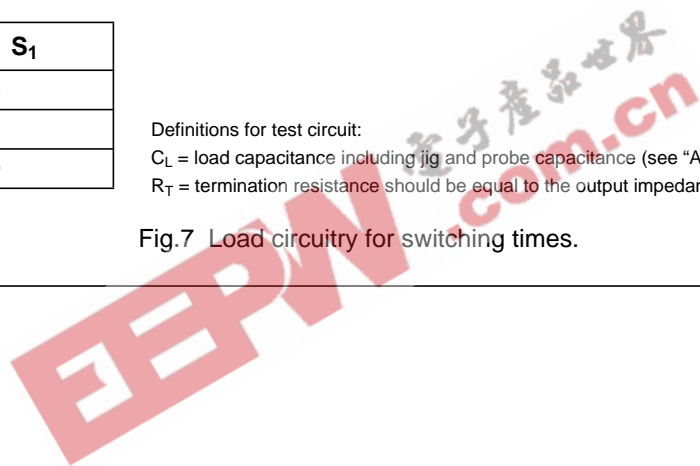
TEST	S ₁
t _{PLH} /t _{PHL}	open
t _{PLZ} /t _{PZL}	V _{CC}
t _{PHZ} /t _{PZH}	GND

Definitions for test circuit:

C_L = load capacitance including jig and probe capacitance (see "AC characteristics").

R_T = termination resistance should be equal to the output impedance Z_o of the pulse generator.

Fig.7 Load circuitry for switching times.



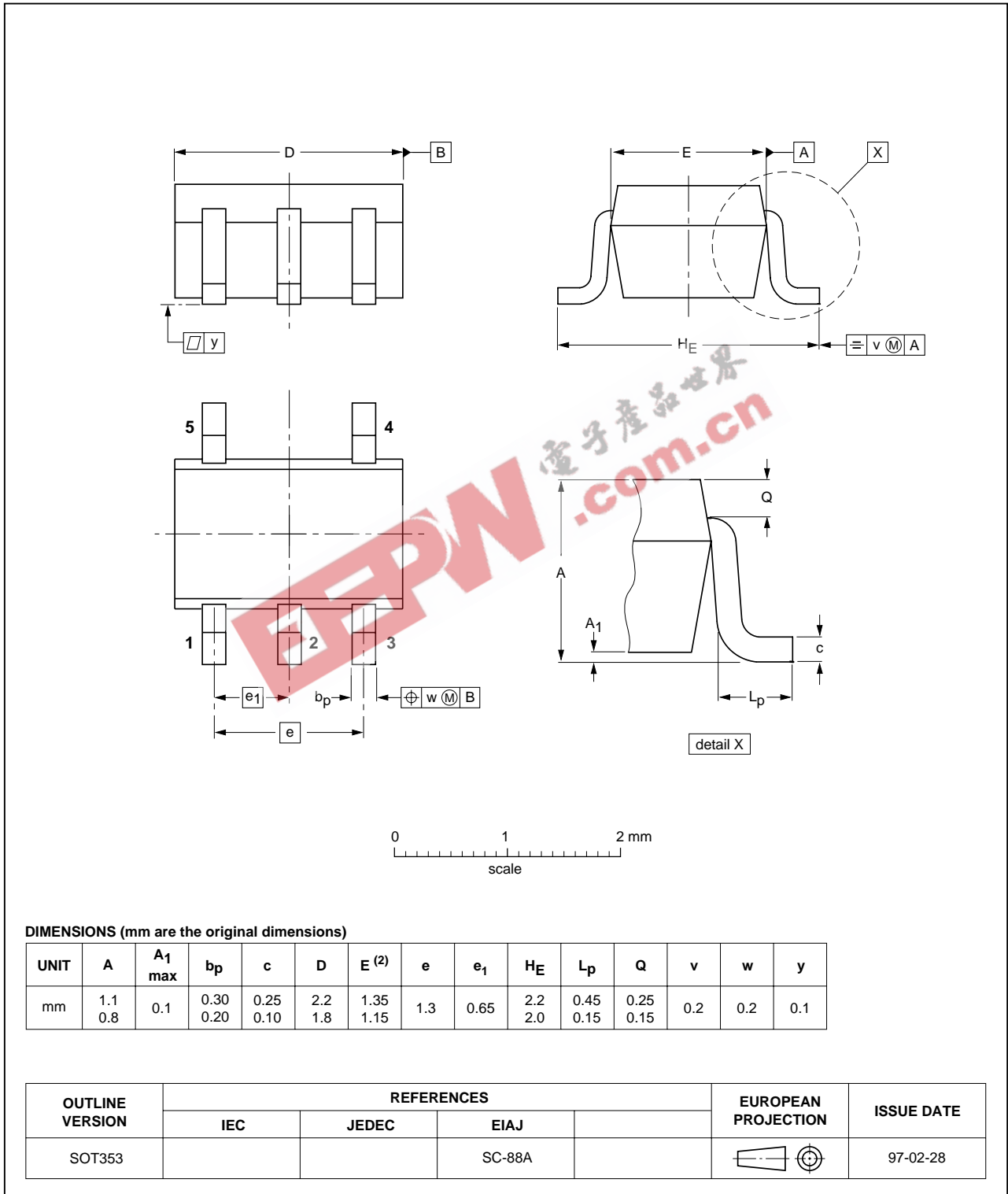
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PACKAGE OUTLINES

Plastic surface mounted package; 5 leads

SOT353

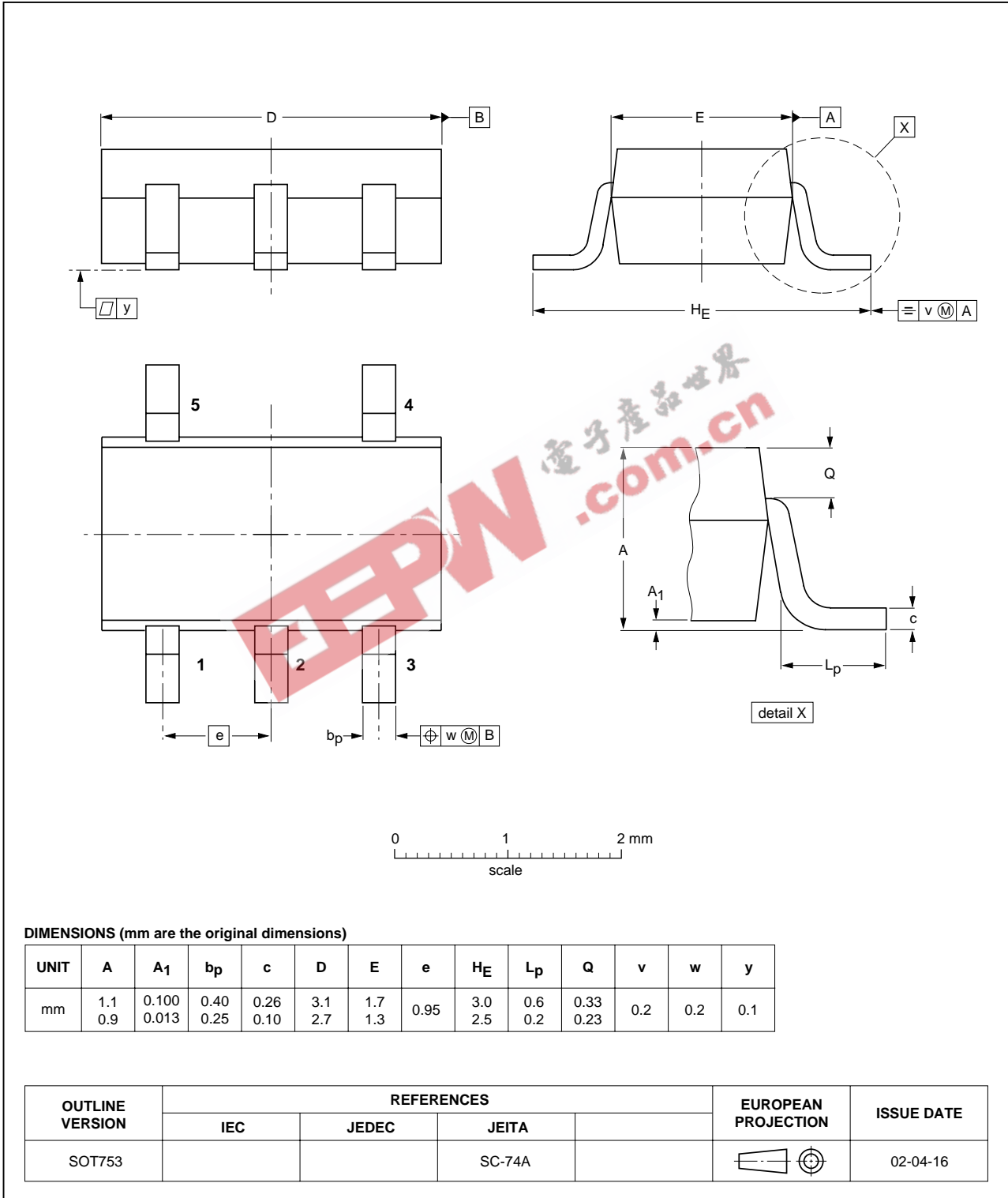


Bus buffer/line drivers; 3-state

74HC1G125; 74HCT1G125

Plastic surface mounted package; 5 leads

SOT753



Bus buffer/line drivers; 3-state

74HC1G125; 74HCT1G125

DATA SHEET STATUS

LEVEL	DATA SHEET STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾⁽³⁾	DEFINITION
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
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Printed in The Netherlands

R44/04/pp13

Date of release: 2004 Jul 27

Document order number: 9397 750 13725

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